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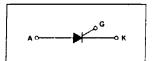
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## 2N6167 thru 2N6170

20 AMPERES RMS 100 thru 600 VOLTS



# Silicon Controlled Rectifier **Reverse Blocking Triode Thyristor**

... designed for industrial and consumer applications such as power supplies; battery chargers; temperature, motor, light and welder controls.

- Economical for a Wide Range of Uses
- High Surge Current ITSM = 240 Amps
  Rugged Construction in Isolated Stud Package

#### **MAXIMUM RATINGS**

Re	iting	Symbol	Value	Unit
*Peak Repetitive Forward and Reverse (T <sub>J</sub> = -40°C to +100°C)	Blocking Voltage (1) 2N6167 2N6168 2N6169 2N6170	VDRM or VRRM	100 200 400 600	Volts
*Non-Repetitive Peak Reverse Blocking (t ≤ 5 ms)	Voltage 2N6167 2N6168 2N6169 2N6170	VRSM	150 250 450 650	Volts
*Average Forward Current (T <sub>C</sub> = -40 to +65°C) (+85°C)		lT(AV)	13 6.5	Amps
*Peek Surge Current (One cycle, 60 Hz) (T <sub>C</sub> = +65°C¹ (1.5 ms pulse @ T <sub>J</sub> = 100°C) Preceded and followed by no current	or Voltage	ITSM	240 560	Amps
Circuit Fusing (T <sub>J</sub> = -40 to +100°C) (t = 1 to 8.3 m	ıs)	12t	235	A <sup>2</sup> s
*Peak Gate Power		PGM	5	Watts
*Average Gate Power	•	PG(AV)	0.5	Watt

NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors** 

<sup>(1)</sup> Ratings apply for zero or negative gate voltage. Devices shall not have a positive bias applied to the gate concurrently with a negative potential on the anode. Devices should not be tested with a constant current source for forward or reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

#### MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit	
*Peak Forward Gate Current	<sup>I</sup> GFM	2	Amps	
*Operating Junction Temperature Range	TJ	-40 to +100	°C	
*Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C	
*Stud Torque	_	30	in. lb.	

### \*THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
ĺ	Thermal Resistance, Junction to Case	Rejc	1.5	°C∕W

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур.	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated VDRM or VRRM, gate open, T <sub>C</sub> = 100°C)	IDRM- IRRM				mA
2N6167 2N6168 2N6169 2N6170 (Rated V <sub>DRM</sub> or V <sub>RRM</sub> , gate open, T <sub>C</sub> = 25°C) All Devices		- - -	1 1 1 1	2 2.5 3 4	ДЦА
*Peak Forward "On" Voltage (I <sub>TM</sub> = 41 A Peak)	∨тм	_	1.5	1.7	Voits
Gate Trigger Current, Continuous dc $^*T_C = -40^{\circ}C$ $(V_D = 12 \text{ V, R}_L = 24 \Omega)$ $^*T_C = 25^{\circ}C$	<sup>I</sup> GT		 2.1	75 40	mA
Gate Trigger Voltage, Continuous dc $^{P}T_{C} = -40^{\circ}C$ $(V_{D} = 12 \text{ V, R}_{L} = 24 \Omega)$ $T_{C} = 25^{\circ}C$	V <sub>GT</sub>	  -	0. <b>8</b> 0. <b>63</b>	2.5 1.6	Volts
Holding Current $^{*}T_{C} = -40^{\circ}C$ $(V_{D} = 12 \text{ V, gate open, }  _{T} = 200 \text{ mA})$ $^{*}T_{C} = 25^{\circ}C$	lH l		 3.5	90 50	mA
*Turn-On Time (t <sub>d</sub> + t <sub>f</sub> ) (I <sub>TM</sub> = 41 Adc, V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>GT</sub> = 200 mAdc, Rise Time ≤ 0.05 μs, Pulse Width = 10 μs)	<sup>t</sup> on	_	-	1	μs
Turn-Off Time (I <sub>TM</sub> = 10 A, I <sub>R</sub> = 10 A) (I <sub>TM</sub> = 10 A, I <sub>R</sub> = 10 A, T <sub>J</sub> = 100°C)	<sup>t</sup> off	_	25 40	_	μs
Forward Voltage Application Rate (T <sub>J</sub> = 100°C, V <sub>D</sub> = Rated V <sub>DRM</sub> )	dv dt		50	-	V/μs

<sup>\*</sup>Indicates JEDEC Registered Data.

